# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



### **Transient Voltage Suppressors**

Low Clamping Voltage Surge Protection Diode Array

The TVS4201MR6 transient voltage suppressor is designed to protect high speed data lines from ESD, EFT, and lightning surges.

#### Features

- Protection for the Following IEC Standards: IEC 61000-4-2 (ESD) ±30 kV (Contact) IEC 61000-4-5 (Lightning) 25 A (8/20 μs)
- Low Clamping Voltage
- Low Leakage
- UL Flammability Rating of 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- High Speed Communication Line Protection
- USB 1.1 and 2.0 Power and Data Line Protection
- Digital Video Interface (DVI)
- Monitors and Flat Panel Displays

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

| Rating   | Symbol           | Value       | Unit |
|--|------------------|-------------|------|
| Peak Power Dissipation 8/20 $\mu$ s @ T <sub>A</sub> = 25°C (Note 1) | P <sub>pk</sub>  | 500         | W    |
| Operating Junction Temperature Range                                 | TJ               | -40 to +125 | °C   |
| Storage Temperature Range  | T <sub>stg</sub> | -55 to +150 | °C   |
| Lead Solder Temperature –<br>Maximum (10 Seconds)                    | ΤL               | 260         | °C   |
| IEC 61000–4–2 Air (ESD)<br>IEC 61000–4–2 Contact (ESD)               | ESD              | ±30<br>±30  | kV   |
| IEC 61000-4-4 (5/50 ns)  | EFT              | 40          | А    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Non-repetitive current pulse per Figure 1 (Pin 5 to Pin 2)

See Application Note AND8308/D for further description of survivability specs.



#### **ON Semiconductor®**

www.onsemi.com



#### MARKING DIAGRAM



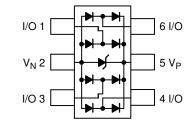
42 = Specific Device Code M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location) \*Date Code orientation may vary

depending upon manufacturing location.

#### PIN CONFIGURATION AND SCHEMATIC



#### **ORDERING INFORMATION**

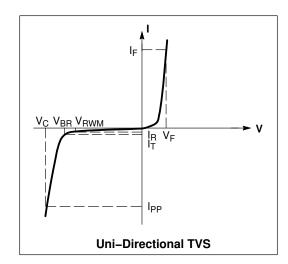
| Device          | Package             | Shipping              |
|-----------------|---------------------|-----------------------|
| TVS4201MR6T1G   | TSOP-6<br>(Pb-Free) | 3000 / Tape &<br>Reel |
| SZTVS4201MR6T1G | TSOP-6<br>(Pb-Free) | 3000 / Tape &<br>Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

| Symbol           | Parameter  |  |
|------------------|--|--|
| I <sub>PP</sub>  | Maximum Reverse Peak Pulse Current                 |  |
| V <sub>C</sub>   | Clamping Voltage @ I <sub>PP</sub>                 |  |
| V <sub>RWM</sub> | Working Peak Reverse Voltage                       |  |
| I <sub>R</sub>   | Maximum Reverse Leakage Current @ V <sub>RWM</sub> |  |
| V <sub>BR</sub>  | Breakdown Voltage @ I <sub>T</sub>                 |  |
| Ι <sub>Τ</sub>   | Test Current                                       |  |
| ١ <sub>F</sub>   | Forward Current                                    |  |
| V <sub>F</sub>   | Forward Voltage @ I <sub>F</sub>                   |  |
| P <sub>pk</sub>  | Peak Power Dissipation                             |  |
| С                | Capacitance @ $V_R = 0$ and f = 1.0 MHz            |  |



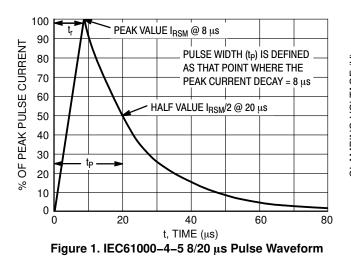
\*See Application Note AND8308/D for detailed explanations of datasheet parameters.

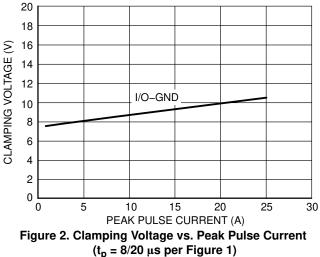
| Parameter                               | Symbol           | Conditions                                     | Min | Тур | Max | Unit |
|---|------------------|--|-----|-----|-----|------|
| Reverse Working Voltage                 | V <sub>RWM</sub> | (Note 2)                                       |     |     | 5.0 | V    |
| Breakdown Voltage                       | V <sub>BR</sub>  | I <sub>T</sub> =1 mA, (Note 3)                 | 6.0 |     |     | V    |
| Reverse Leakage Current                 | I <sub>R</sub>   | V <sub>RWM</sub> = 5 V                         |     |     | 1.0 | μΑ   |
| Clamping Voltage                        | V <sub>C</sub>   | I <sub>PP</sub> = 1 A, Any I/O to GND          |     |     | 8.5 | V    |
| (t <sub>p</sub> = 8/20 μs per Figure 1) |                  | I <sub>PP</sub> = 5 A, Any I/O to GND          |     |     | 9.0 |      |
|   |                  | I <sub>PP</sub> = 8 A, Any I/O to GND          |     |     | 10  |      |
|   |                  | I <sub>PP</sub> = 25 A, Any I/O to GND         |     |     | 12  |      |
| Junction Capacitance                    | CJ               | $V_R = 0 V$ , f=1 MHz between I/O Pins and GND |     | 3.0 | 5.0 | pF   |
| Junction Capacitance                    | CJ               | $V_R = 0 V$ , f=1 MHz between I/O Pins         |     | 1.5 | 3.0 | pF   |

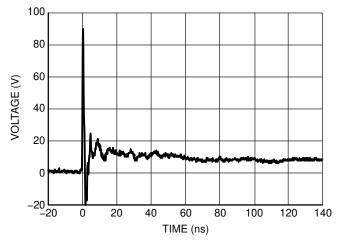
ELECTRICAL CHARACTERISTICS (TJ=25°C unless otherwise specified)

TVS devices are normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal or greater than the DC or continuous peak operating voltage level.

3. V<sub>BR</sub> is measured at pulse test current I<sub>T</sub>.







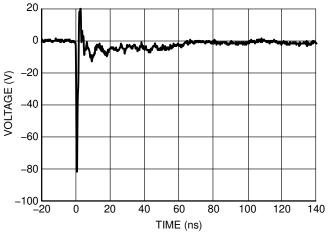
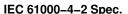
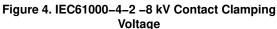
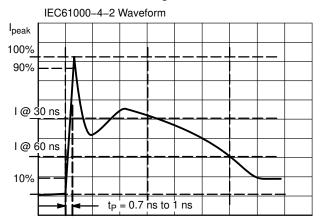


Figure 3. IEC61000–4–2 +8 kV Contact Clamping Voltage



| Level | Test Volt-<br>age (kV) | First Peak<br>Current<br>(A) | Current at<br>30 ns (A) | Current at<br>60 ns (A) |
|-------|------------------------|------------------------------|-------------------------|-------------------------|
| 1     | 2                      | 7.5                          | 4                       | 2                       |
| 2     | 4                      | 15                           | 8                       | 4                       |
| 3     | 6                      | 22.5                         | 12                      | 6                       |
| 4     | 8                      | 30                           | 16                      | 8                       |







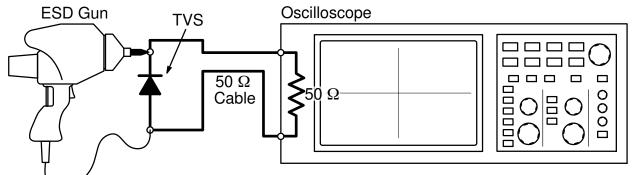


Figure 6. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

#### **ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

#### **TYPICAL PERFORMANCE CURVES**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

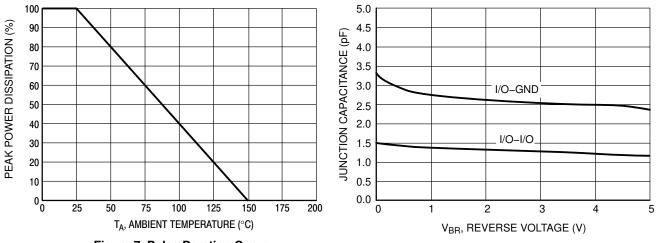




Figure 8. Junction Capacitance vs Reverse Voltage

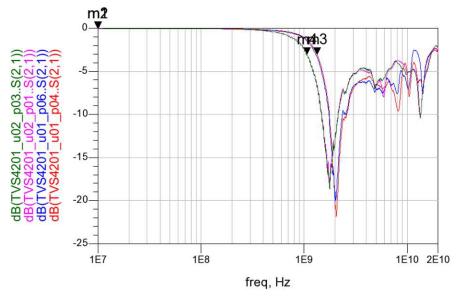


Figure 9. RF Insertion Loss



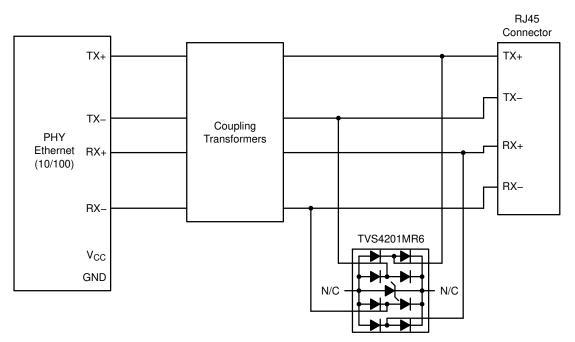


Figure 10. Protection for Ethernet 10/100 (Differential mode)

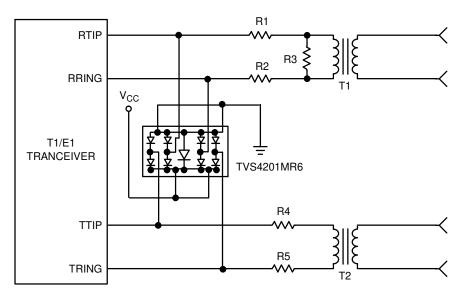
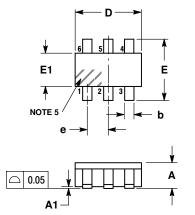


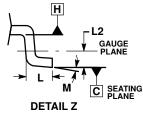
Figure 11. TI/E1 Interface Protection

#### PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 **ISSUE V** 

NOTES





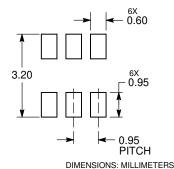


DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM З.
- MAXIMUM LEAD FHICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
  PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

|     | MILLIMETERS |      |      |
|-----|-------------|------|------|
| DIM | MIN         | NOM  | MAX  |
| Α   | 0.90        | 1.00 | 1.10 |
| A1  | 0.01        | 0.06 | 0.10 |
| b   | 0.25        | 0.38 | 0.50 |
| С   | 0.10        | 0.18 | 0.26 |
| D   | 2.90        | 3.00 | 3.10 |
| Е   | 2.50        | 2.75 | 3.00 |
| E1  | 1.30        | 1.50 | 1.70 |
| е   | 0.85        | 0.95 | 1.05 |
| L   | 0.20        | 0.40 | 0.60 |
| L2  | 0.25 BSC    |      |      |
| М   | 0°          | -    | 10°  |

#### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the unarrest are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative